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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1007dana-u0

Table 1-1. List of Ordering Part Numbers

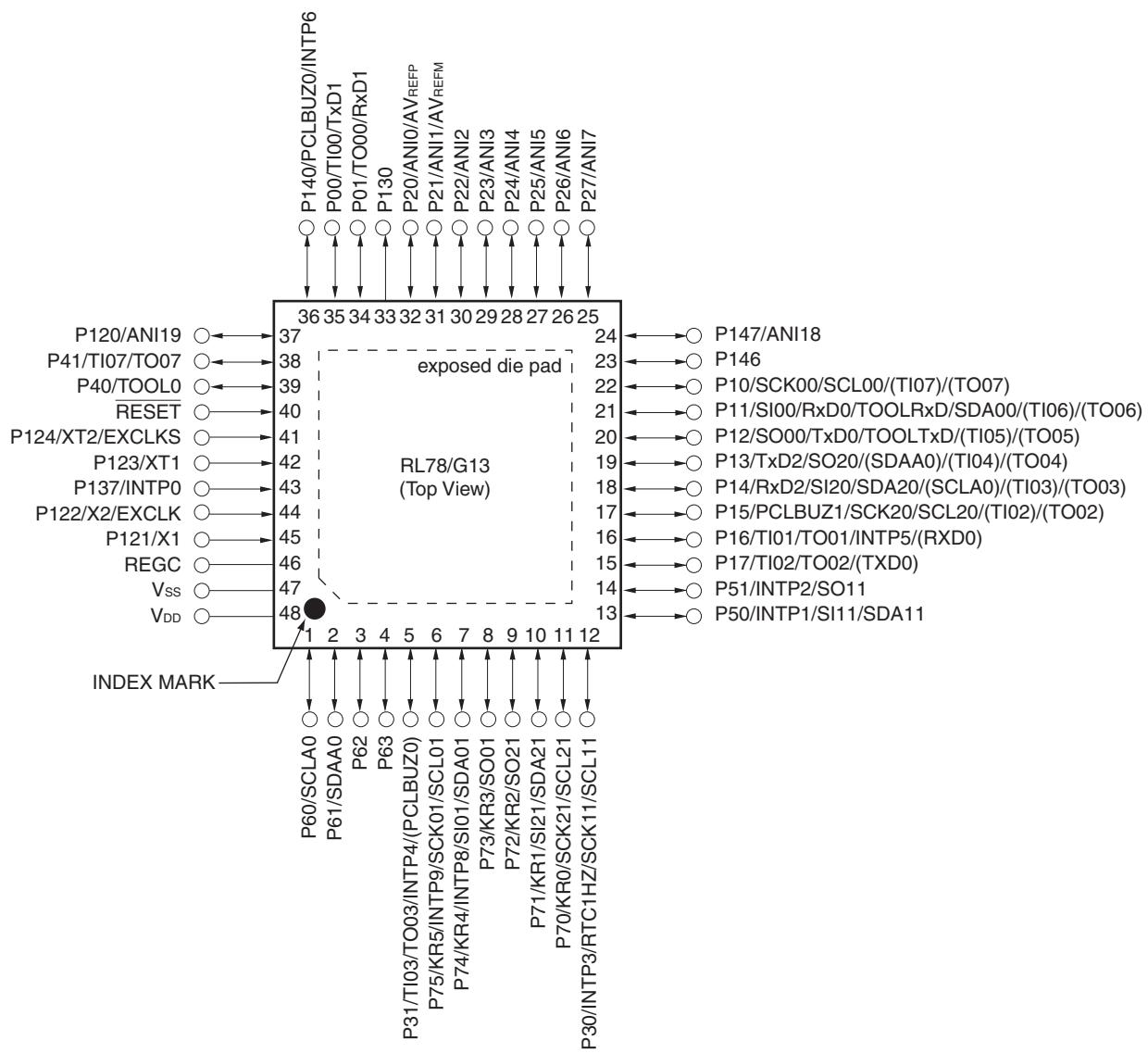
(4/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A D G	R5F100FAAFP#V0, R5F100FC AFP#V0, R5F100FDAFP#V0, R5F100FEA FP#V0, R5F100FFA FP#V0, R5F100FGA FP#V0, R5F100FH A FP#V0, R5F100FJA FP#V0, R5F100FKA FP#V0, R5F100FLA FP#V0 R5F100FAAFP#X0, R5F100FC AFP#X0, R5F100FDAFP#X0, R5F100FEA FP#X0, R5F100FFA FP#X0, R5F100FGA FP#X0, R5F100FH A FP#X0, R5F100FJA FP#X0, R5F100FKA FP#X0, R5F100FLA FP#X0 R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0 R5F100FAGFP#V0, R5F100FC GFP#V0, R5F100FD GFP#V0, R5F100FEGFP#V0, R5F100FF GFP#V0, R5F100FG GFP#V0, R5F100FH GFP#V0, R5F100FJ GFP#V0 R5F100FAGFP#X0, R5F100FC GFP#X0, R5F100FD GFP#X0, R5F100FEGFP#X0, R5F100FF GFP#X0, R5F100FG GFP#X0, R5F100FH GFP#X0, R5F100FJ GFP#X0 Not mounted
			A D	R5F101FAAFP#V0, R5F101FC AFP#V0, R5F101FDAFP#V0, R5F101FEA FP#V0, R5F101FFA FP#V0, R5F101FGA FP#V0, R5F101FH A FP#V0, R5F101FJA FP#V0, R5F101FKA FP#V0, R5F101FLA FP#V0 R5F101FAAFP#X0, R5F101FC AFP#X0, R5F101FDAFP#X0, R5F101FEA FP#X0, R5F101FFA FP#X0, R5F101FGA FP#X0, R5F101FH A FP#X0, R5F101FJA FP#X0, R5F101FKA FP#X0, R5F101FLA FP#X0 R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 48-pin plastic HWQFN (7×7 mm, 0.5 mm pitch)



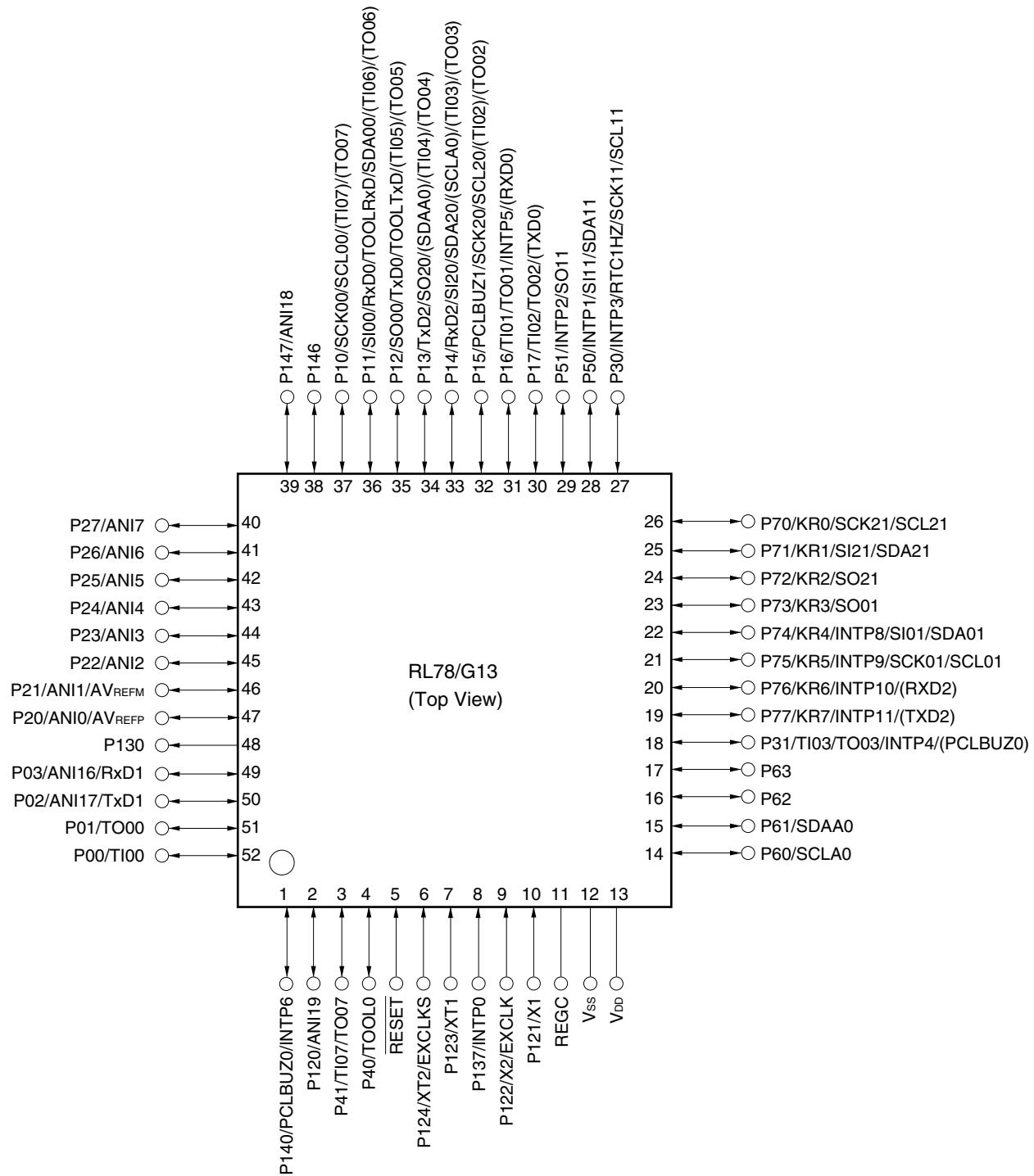
Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
3. It is recommended to connect an exposed die pad to V_{SS}.

1.3.10 52-pin products

- 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)

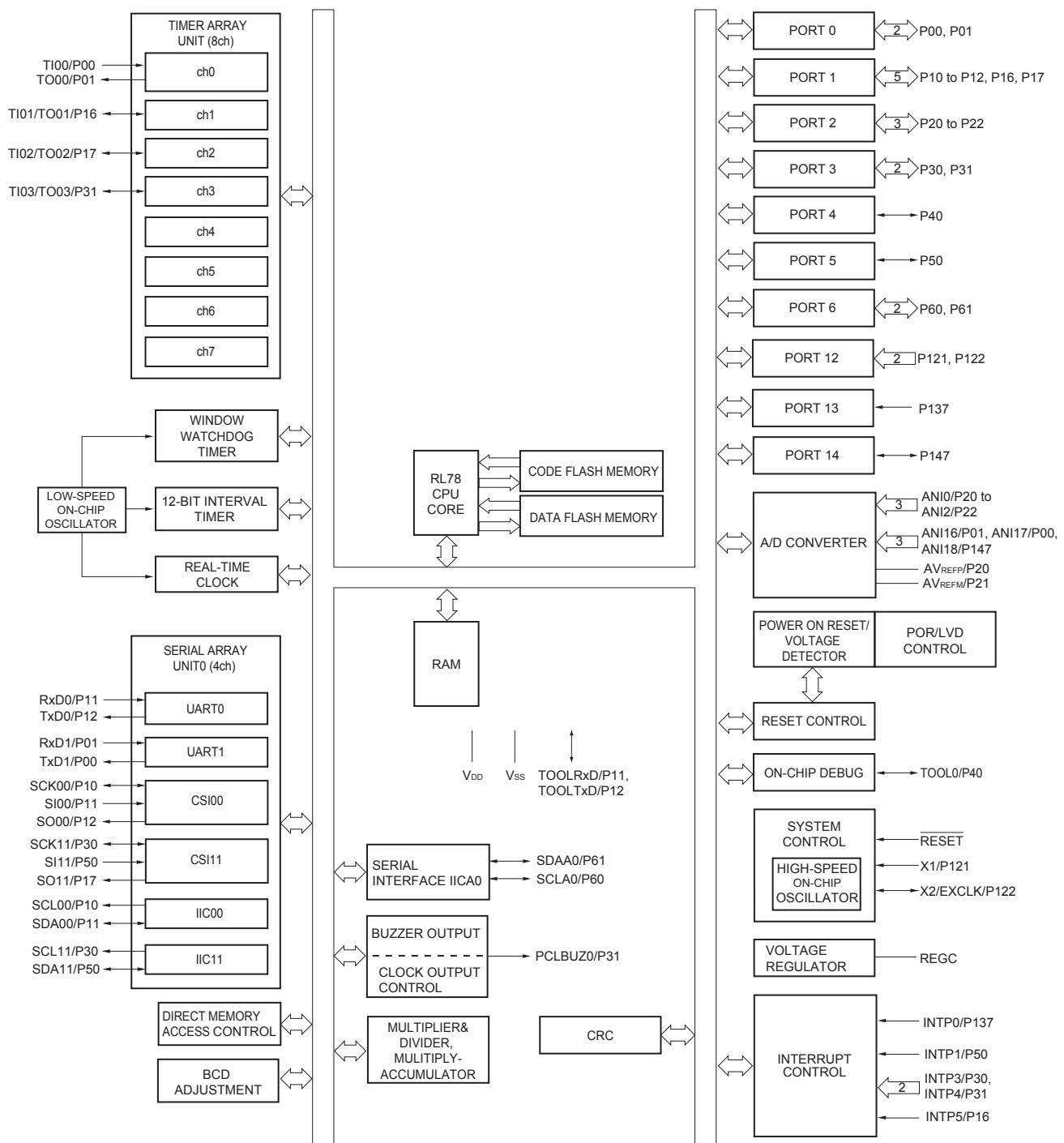


Caution Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

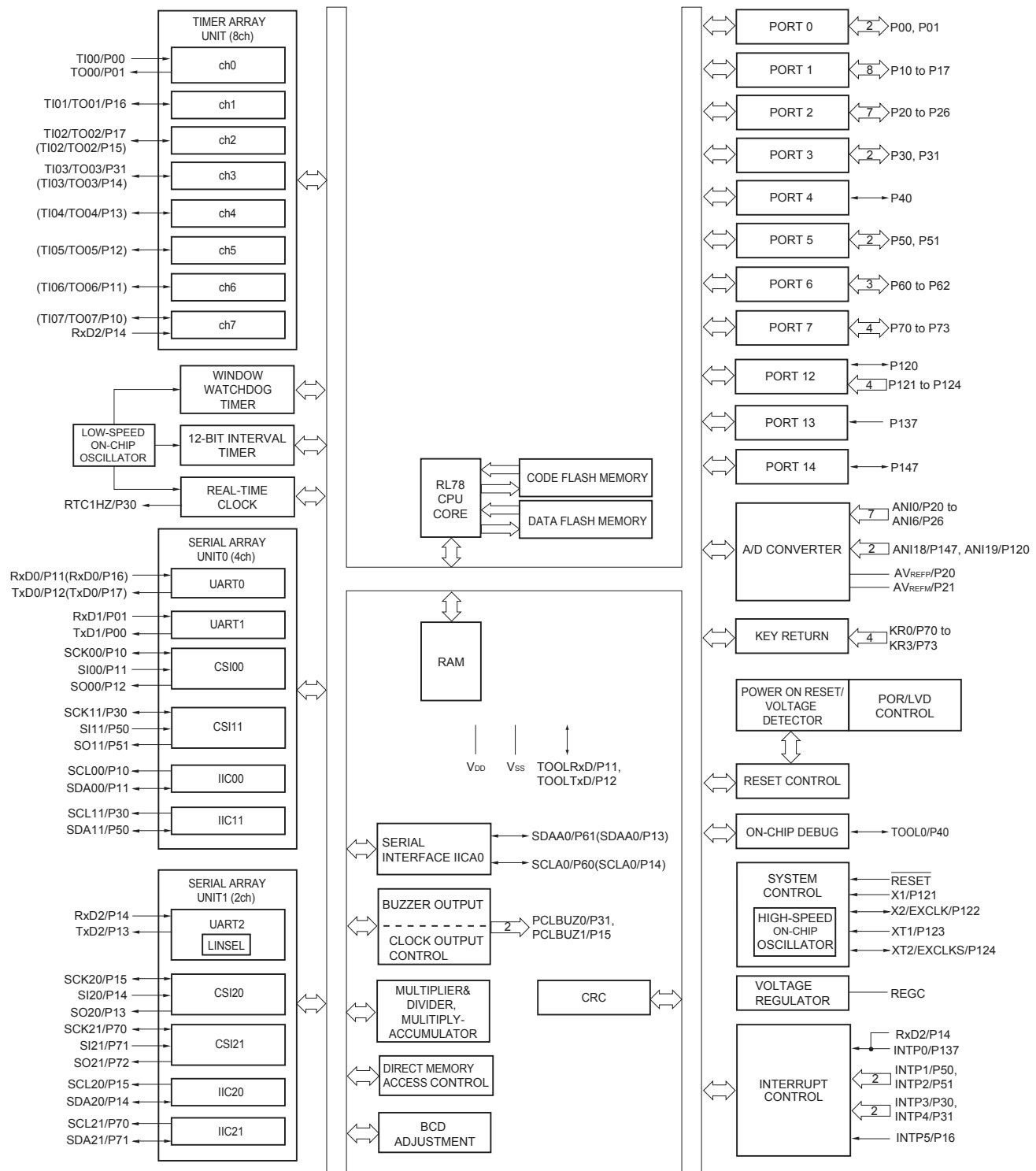
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.2 24-pin products

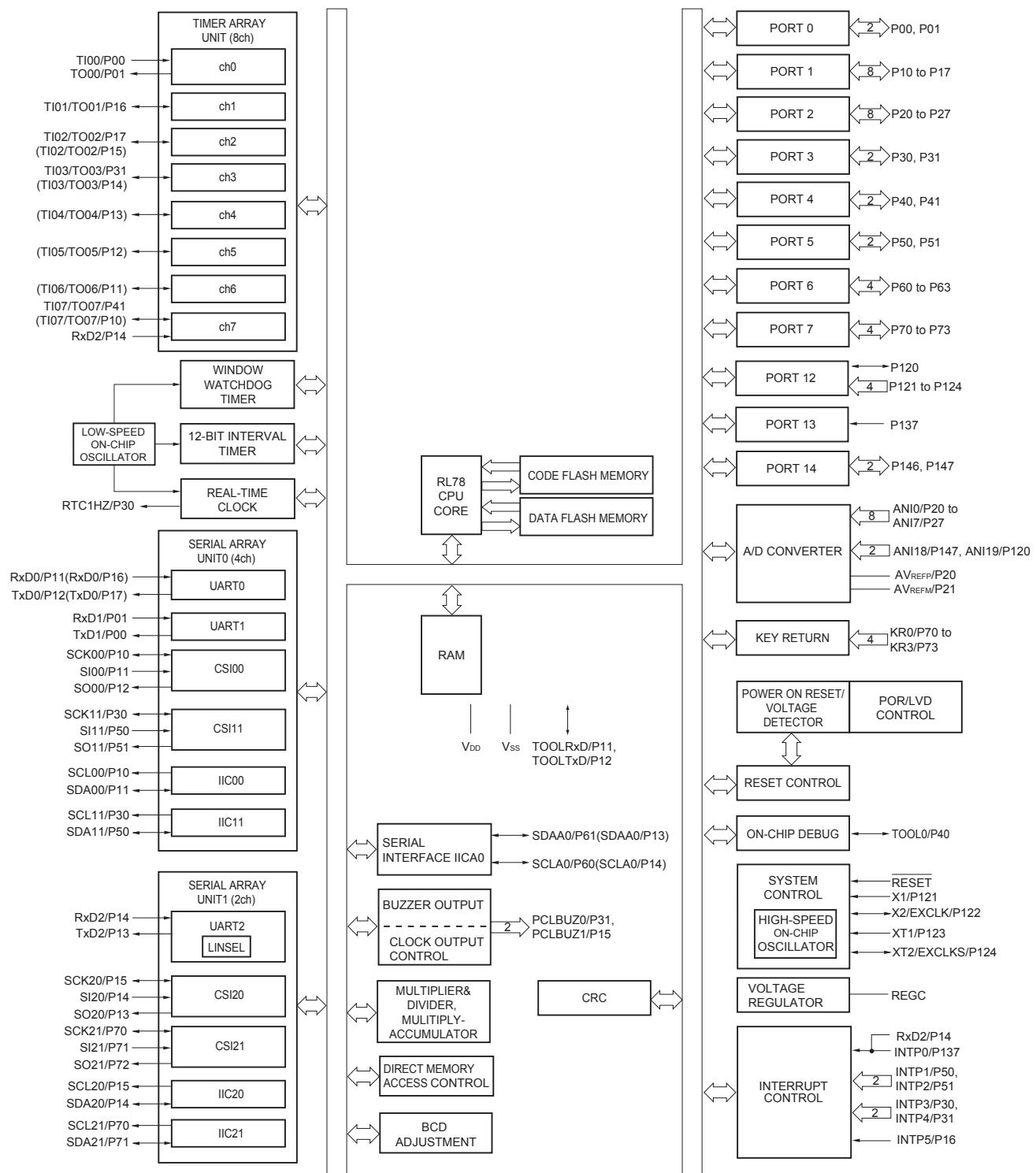


1.5.7 40-pin products



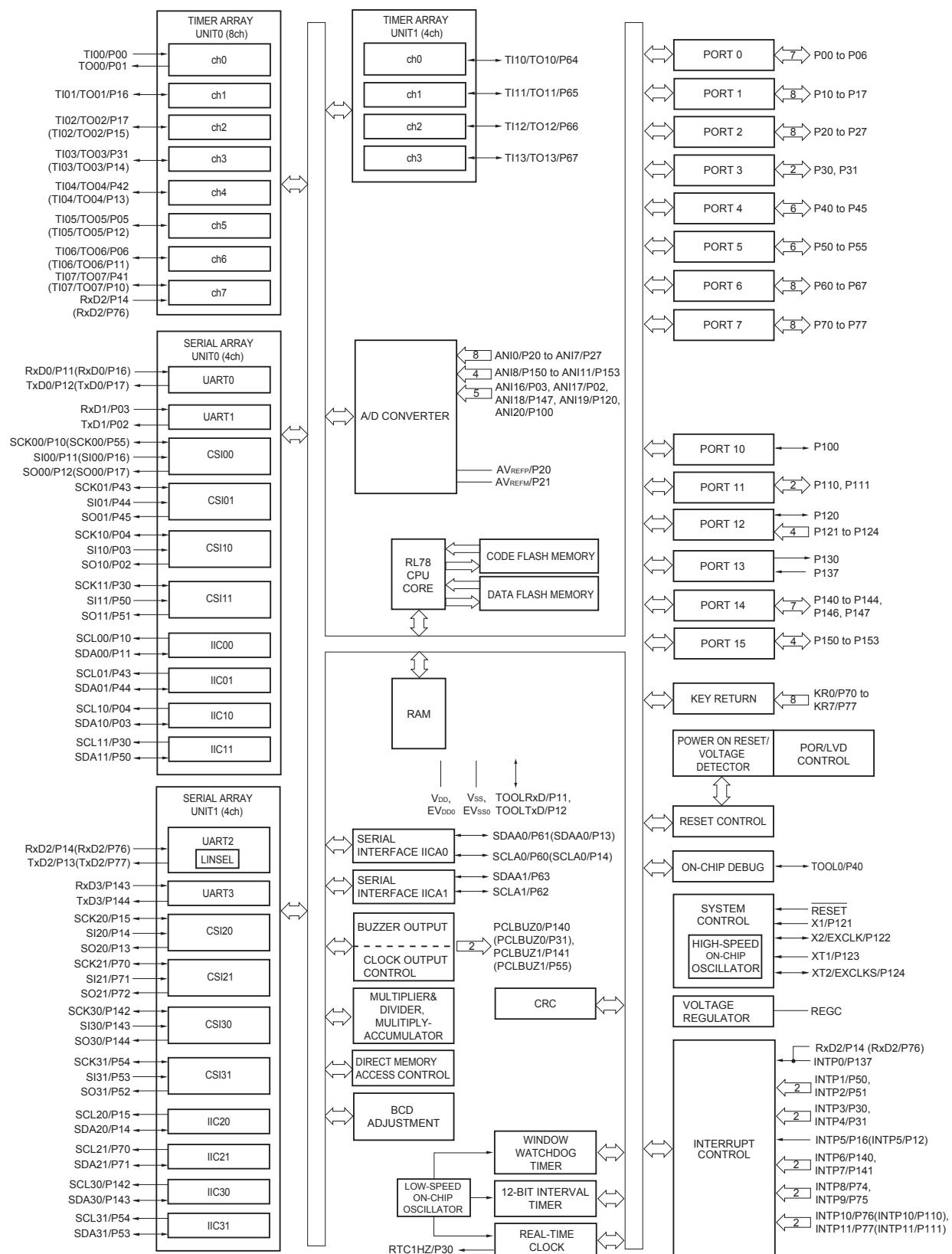
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.8 44-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

Item	20-pin		24-pin		25-pin		30-pin		32-pin		36-pin											
	R5F1006X	R5F1016X	R5F1007X	R5F1017X	R5F1008X	R5F1018X	R5F100AX	R5F101AX	R5F100BX	R5F101BX	R5F100CX	R5F101CX										
Code flash memory (KB)	16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128											
Data flash memory (KB)	4	—	4	—	4	—	4 to 8	—	4 to 8	—	4 to 8	—										
RAM (KB)	2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}											
Address space	1 MB																					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																				
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																				
Subsystem clock	—																					
Low-speed on-chip oscillator	15 kHz (TYP.)																					
General-purpose registers	(8-bit register × 8) × 4 banks																					
Minimum instruction execution time	0.03125 μ s (High-speed on-chip oscillator: $f_{IH} = 32$ MHz operation)																					
	0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)																					
Instruction set	<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 																					
I/O port	Total	16	20	21	26	28	32															
	CMOS I/O	13 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)	15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)	15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)	21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	22 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	26 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)															
	CMOS input	3	3	3	3	3	3															
	CMOS output	—	—	1	—	—	—															
	N-ch O.D. I/O (withstand voltage: 6 V)	—	2	2	2	3	3															
Timer	16-bit timer	8 channels																				
	Watchdog timer	1 channel																				
	Real-time clock (RTC)	1 channel ^{Note 2}																				
	12-bit interval timer (IT)	1 channel																				
	Timer output	3 channels (PWM outputs: 2 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3}), 8 channels (PWM outputs: 7 ^{Note 3}) ^{Note 4}																		
	RTC output	—																				

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (2/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147			20.0 ^{Note 2}	mA
		Per pin for P60 to P63			15.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty $\leq 70\%$ ^{Note 3})	4.0 V \leq EV _{DD0} \leq 5.5 V		70.0	mA
			2.7 V \leq EV _{DD0} $<$ 4.0 V		15.0	mA
			1.8 V \leq EV _{DD0} $<$ 2.7 V		9.0	mA
			1.6 V \leq EV _{DD0} $<$ 1.8 V		4.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq 70\%$ ^{Note 3})	4.0 V \leq EV _{DD0} \leq 5.5 V		80.0	mA
			2.7 V \leq EV _{DD0} $<$ 4.0 V		35.0	mA
			1.8 V \leq EV _{DD0} $<$ 2.7 V		20.0	mA
			1.6 V \leq EV _{DD0} $<$ 1.8 V		10.0	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})			150.0	mA
	I _{OL2}	Per pin for P20 to P27, P150 to P156			0.4 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	1.6 V \leq V _{DD} \leq 5.5 V		5.0	mA

- Notes**
- Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EV_{SS0}, EV_{SS1} and V_{SS} pin.
 - However, do not exceed the total current value.
 - Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor $> 70\%$ the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and I_{OL} = 10.0 mA

$$\text{Total output current of pins} = (10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer 0.8EV _{DD0}		EV _{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V \leq EV _{DD0} \leq 5.5 V	2.2		EV _{DD0}
			TTL input buffer 3.3 V \leq EV _{DD0} < 4.0 V	2.0		EV _{DD0}
			TTL input buffer 1.6 V \leq EV _{DD0} < 3.3 V	1.5		EV _{DD0}
	V_{IH3}	P20 to P27, P150 to P156	0.7V _{DD}		V _{DD}	V
	V_{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer 0		0.2EV _{DD0}	V
	V_{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V \leq EV _{DD0} \leq 5.5 V	0		0.8
			TTL input buffer 3.3 V \leq EV _{DD0} < 4.0 V	0		0.5
			TTL input buffer 1.6 V \leq EV _{DD0} < 3.3 V	0		0.32
	V_{IL3}	P20 to P27, P150 to P156	0		0.3V _{DD}	V
	V_{IL4}	P60 to P63	0		0.3EV _{DD0}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note The following conditions are required for low voltage interface when $\text{EV}_{\text{DD}0} < \text{V}_{\text{DD}}$

$1.8 \text{ V} \leq \text{EV}_{\text{DD}0} < 2.7 \text{ V}$: MIN. 125 ns

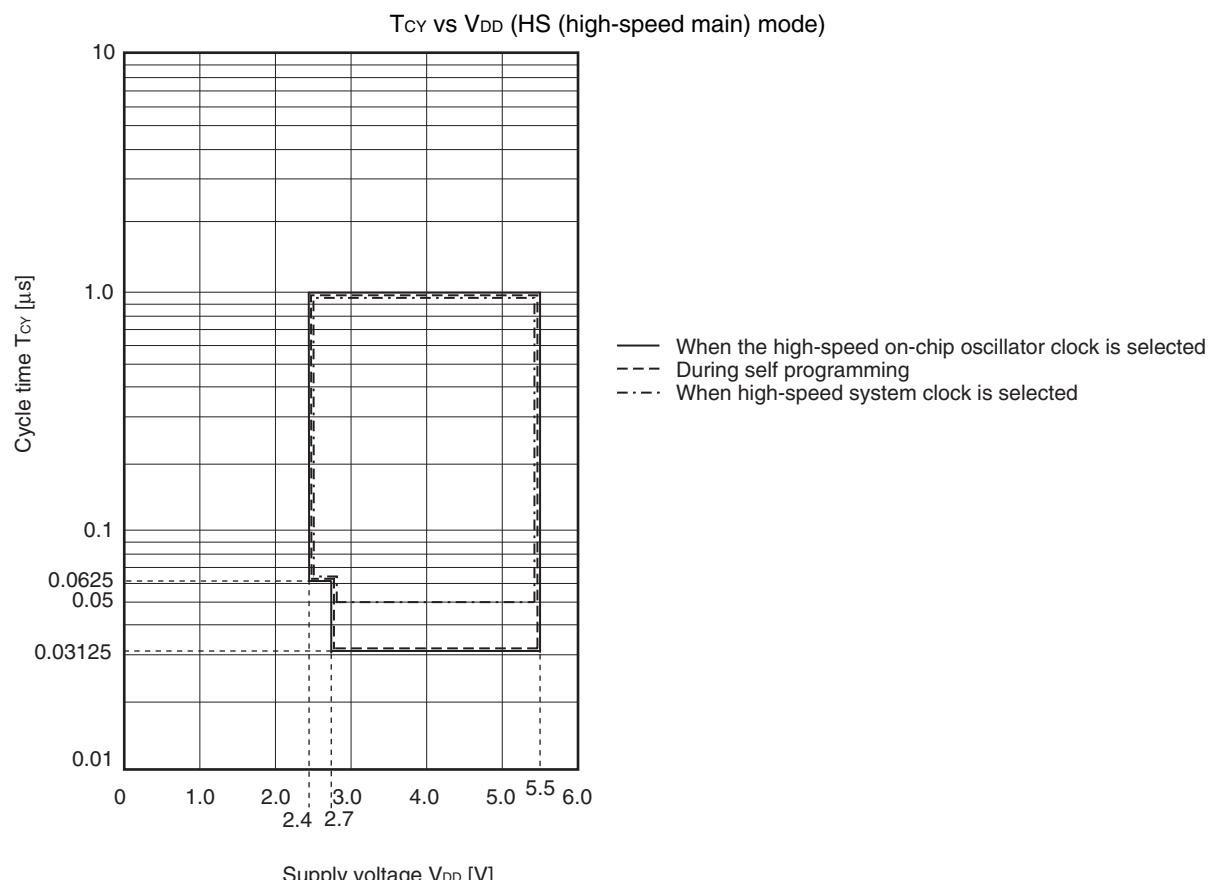
$1.6 \text{ V} \leq \text{EV}_{\text{DD}0} < 1.8 \text{ V}$: MIN. 250 ns

Remark f_{MCK} : Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t _{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V $\leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			2.4 V $\leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			1.8 V $\leq EV_{DD0} \leq 5.5$ V	500		500		1000		ns
			1.7 V $\leq EV_{DD0} \leq 5.5$ V	1000		1000		1000		ns
			1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		1000		1000		ns
SCKp high-/low-level width	t _{Kh1} , t _{kl1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 38		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
Slp setup time (to SCKp↑) <small>Note 1</small>	t _{SIK1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	75		110		110		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	110		110		110		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	220		220		220		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		220		220		ns	
Slp hold time (from SCKp↑) <small>Note 2</small>	t _{ksi1}	1.7 V $\leq EV_{DD0} \leq 5.5$ V	19		19		19		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		19		19		ns	
Delay time from SCKp↓ to SOp output <small>Note 3</small>	t _{ks01}	1.7 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		25		25		25	ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		—		25		25	ns	

- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)
(1/3)**

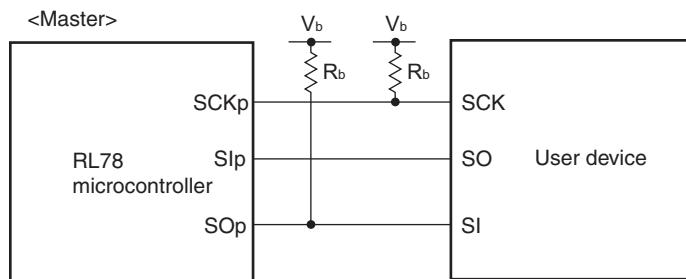
($T_A = -40$ to $+85^\circ\text{C}$, $1.8 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	300		1150		1150		ns
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	500		1150		1150		ns
			1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t _{Kh1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 75		t _{KCY1} /2 – 75		t _{KCY1} /2 – 75			ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 170		t _{KCY1} /2 – 170		t _{KCY1} /2 – 170			ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 458		t _{KCY1} /2 – 458		t _{KCY1} /2 – 458			ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50			ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50			ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50			ns

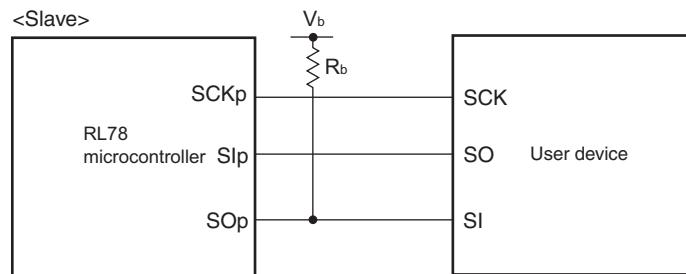
Note Use it with $EV_{DD0} \geq V_b$.

Caution Select the TTL input buffer for the S_{Op} pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the S_{Op} pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SO_p) pull-up resistance, $C_b[F]$: Communication line (SO_p) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -3.0 mA	EV _{DD0} – 0.7		V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -2.0 mA	EV _{DD0} – 0.6		V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -1.5 mA	EV _{DD0} – 0.5		V
	V _{OH2}	P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH2} = -100 μA	V _{DD} – 0.5		V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 8.5 mA		0.7	V
			4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 3.0 mA		0.6	V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 1.5 mA		0.4	V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 0.6 mA		0.4	V
	V _{OL2}	P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OL2} = 400 μA		0.4	V
	V _{OL3}	P60 to P63	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 15.0 mA		2.0	V
			4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 5.0 mA		0.4	V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 3.0 mA		0.4	V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 2.0 mA		0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.
3. When high-speed system clock and subsystem clock are stopped.
4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $AMPHS1 = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz
 $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH} : High-speed on-chip oscillator clock frequency
3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{IH} = 32 \text{ MHz}$ ^{Note 3}	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		2.3		mA
					Normal operation	$V_{DD} = 5.0 \text{ V}$		5.2	9.2	mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		5.2	9.2	mA
				$f_{IH} = 24 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 5.0 \text{ V}$		4.1	7.0	mA
					Normal operation	$V_{DD} = 3.0 \text{ V}$		4.1	7.0	mA
		HS (high-speed main) mode Note 5	$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
				Normal operation	Square wave input		3.4	5.9		mA
				Normal operation	Resonator connection		3.6	6.0		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		2.1	3.5		mA
				Normal operation	Resonator connection		2.1	3.5		mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9		μA
				Normal operation	Resonator connection		4.9	6.0		μA
				Normal operation	Square wave input		4.9	5.9		μA
				Normal operation	Resonator connection		5.0	6.0		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6		μA
				Normal operation	Resonator connection		5.1	7.7		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3		μA
				Normal operation	Resonator connection		5.3	9.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3		μA
				Normal operation	Resonator connection		5.8	13.4		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		10.0	46.0		μA
				Normal operation	Resonator connection		10.0	46.0		μA

(Notes and Remarks are listed on the next page.)

3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	2.4 V ≤ V _{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites <small>Notes 1,2,3</small>	C _{erwr}	Retained for 20 years TA = 85°C <small>Note 4</small>	1,000			Times
		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C <small>Note 4</small>	100,000			
		Retained for 20 years TA = 85°C <small>Note 4</small>	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library.
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

Revision History		RL78/G13 Data Sheet	
Rev.	Date	Description	
		Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing